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(71) Applicant (for all designated States except US): **TINGGI  
TECHNOLOGIES PRIVATE LIMITED** [SG/SG]; 83  
Science Park Drive, #03-01/02, The Curie, Science Park 1,  
Singapore 118258 (SG).

(72) Inventors; and

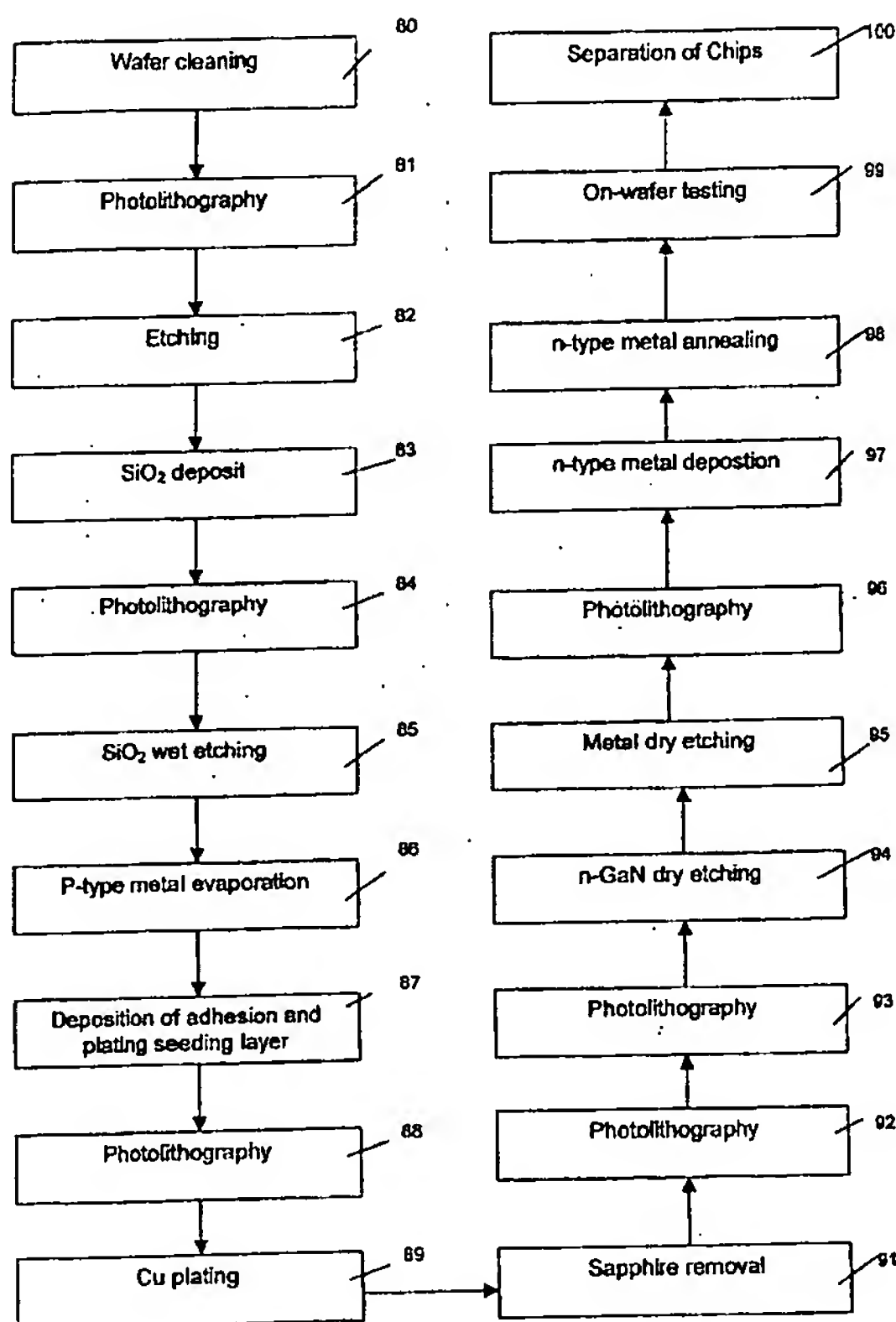
(75) Inventors/Applicants (for US only): **KANG, Xuejun**  
[CN/SG]; Block 509, West Coast Drive, #11-277, Sin-  
gapore 120509, 120509 Singapore (SG). **WU, Dalke**  
[CN/SG]; Block 527, Jelepang Road, #07-603, Singa-  
pore 670527, 670527 Singapore (SG). **PERRY, Edward  
Robert** [US/US]; 2440 Sanborn Drive, Sedona, Arizona  
86336, USA, Sedona, AZ 86336 (US).

(74) Agent: **ALBAN TAY MAHTANI & DE SILVA**; 39  
Robinson Road, #07-01 Robinson Point, Singapore  
068911, 068911 Singapore (SG).

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(54) Title: FABRICATION OF SEMICONDUCTOR DEVICES



(57) Abstract: A method for fabrication of a semiconductor device on a substrate, the semiconductor having a wafer. The method includes the steps: (a) applying a seed layer of a thermally conductive metal to the wafer; (b) electroplating a relatively thick layer of the conductive metal on the seed layer; and (c) removing the substrate. A corresponding semiconductor device is also disclosed.



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